

Wei Mi

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4023872/publications.pdf>

Version: 2024-02-01

22
papers

565
citations

687363

13
h-index

794594

19
g-index

22
all docs

22
docs citations

22
times ranked

778
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of oxygen flow ratio on crystallization and structural characteristics of gallium oxide thin films. <i>Ceramics International</i> , 2022, 48, 3751-3756.	4.8	6
2	Optoelectronic artificial synapses based on \hat{I}^2 -Ga ₂ O ₃ films by RF magnetron sputtering. <i>Vacuum</i> , 2021, 192, 110422.	3.5	23
3	A solar-blind photodetector based on \hat{I}^2 -Ga ₂ O ₃ film deposited on MgO (100) substrates by RF magnetron sputtering. <i>Vacuum</i> , 2020, 180, 109632.	3.5	22
4	Resistive random access memory based on gallium oxide thin films for self-powered pressure sensor systems. <i>Ceramics International</i> , 2020, 46, 21141-21148.	4.8	14
5	Effect of electrode materials and annealing on metal-semiconductor contact of Ga ₂ O ₃ with metal. <i>Optoelectronics Letters</i> , 2020, 16, 118-121.	0.8	3
6	Gate Tunable Memtransistor based on Monolayer Molybdenum Disulfide. , 2020, , .		0
7	Performance Optimization of HFOx-Based Transparent Resistance Random Access Memory. , 2019, , .		0
8	Influence of annealing on the structural and optical properties of gallium oxide films deposited on c-sapphire substrate. <i>Vacuum</i> , 2019, 167, 6-9.	3.5	24
9	Synthesis of monoclinic structure gallium oxide film on sapphire substrate by magnetron sputtering. <i>Optoelectronics Letters</i> , 2017, 13, 295-298.	0.8	5
10	Effect of annealing on the properties of Ga ₂ O ₃ :Mg films prepared on \hat{I}^2 -Al ₂ O ₃ (0001) by MOCVD. <i>Vacuum</i> , 2016, 124, 101-107.	3.5	37
11	Annealing effect on the optical and electronic properties of \hat{I}^2 -Ga ₂ O ₃ /AZO multilayered films. <i>Journal of Materials Science: Materials in Electronics</i> , 2016, 27, 11390-11395.	2.2	4
12	Influence of annealing on the structural, optical and electrical properties of indium oxide films deposited on c-sapphire substrate. <i>Optoelectronics Letters</i> , 2016, 12, 39-42.	0.8	0
13	Mg-doped \hat{I}^2 -Ga ₂ O ₃ films with tunable optical band gap prepared on MgO (110) substrates by metal-organic chemical vapor deposition. <i>Materials Science in Semiconductor Processing</i> , 2015, 34, 52-57.	4.0	33
14	Synthesis of Large-Area Highly Crystalline Monolayer Molybdenum Disulfide with Tunable Grain Size in a H ₂ Atmosphere. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 22587-22593.	8.0	47
15	Characterization of Sn-doped \hat{I}^2 -Ga ₂ O ₃ films deposited on MgO (100) substrate by MOCVD. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 7889-7894.	2.2	16
16	Transparent conducting tin-doped Ga ₂ O ₃ films deposited on MgAl ₂ O ₄ (100) substrates by MOCVD. <i>Ceramics International</i> , 2015, 41, 2572-2575.	4.8	31
17	Structural and optical properties of \hat{I}^2 -Ga ₂ O ₃ films deposited on MgAl ₂ O ₄ (1 0 0) substrates by metal-organic chemical vapor deposition. <i>Journal of Luminescence</i> , 2014, 146, 1-5.	3.1	56
18	Effect of Sb doping on structural, electrical and optical properties of epitaxial SnO ₂ films grown on r-cut sapphire. <i>Journal of Alloys and Compounds</i> , 2014, 586, 426-430.	5.5	17

#	ARTICLE	IF	CITATIONS
19	Preparation and characterization of single crystalline In ₂ O ₃ films deposited on MgO (110) substrates by MOCVD. <i>Ceramics International</i> , 2014, 40, 4203-4206.	4.8	6
20	Ultraviolet-green photoluminescence of $\hat{\Gamma}^2$ -Ga ₂ O ₃ films deposited on MgAl ₆ O ₁₀ (100) substrate. <i>Optical Materials</i> , 2013, 35, 2624-2628.	3.6	52
21	Characterization of $\hat{\Gamma}^2$ -Ga ₂ O ₃ thin films on sapphire (0001) using metal-organic chemical vapor deposition technique. <i>Vacuum</i> , 2012, 86, 1850-1854.	3.5	92
22	Structural and optical properties of heteroepitaxial beta Ga ₂ O ₃ films grown on MgO (100) substrates. <i>Thin Solid Films</i> , 2012, 520, 4270-4274.	1.8	77